

isc Silicon NPN Power Transistors

BUX67/A/B/C

DESCRIPTION

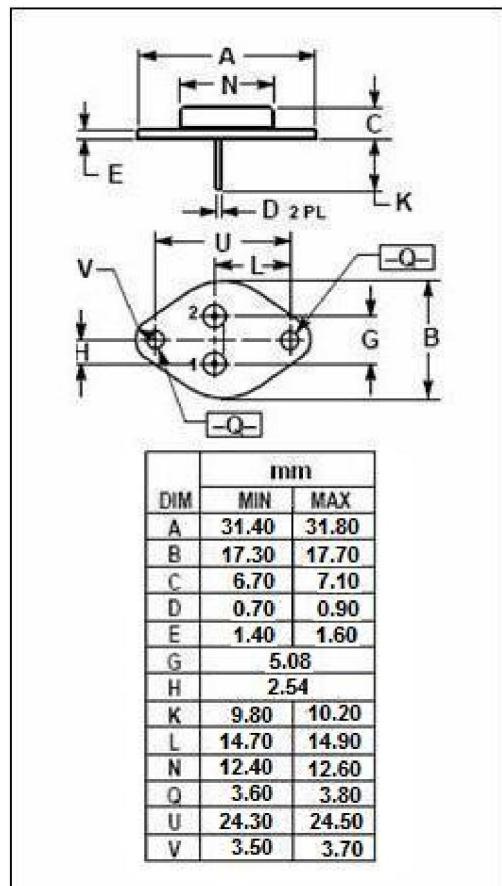
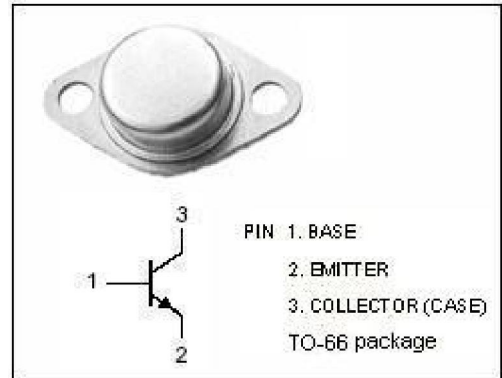
- Continuous Collector Current- $I_C= 2A$
- Power Dissipation- $P_D=35W @T_C= 25^\circ C$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)}= 2.5V(Max)@ I_C = 1A$

APPLICATIONS

- Designed for high-speed switching and linear amplifier application for high-voltage operational amplifiers, switching regulators, converters, deflection stages and high fidelity amplifiers.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT	
V_{CBO}	Collector-Base Voltage	BUX67	200	V
		BUX67A	300	
		BUX67B	350	
		BUX67C	400	
V_{CEO}	Collector-Emitter Voltage	BUX67	150	V
		BUX67A	250	
		BUX67B	300	
		BUX67C	350	
V_{EBO}	Emitter-Base Voltage	6	V	
I_C	Collector Current-Continuous	2.0	A	
I_{CP}	Collector Current-Peak	5.0	A	
I_B	Base Current	1.0	A	
P_C	Collector Power Dissipation@ $T_C=25^\circ C$	35	W	
T_J	Junction Temperature	200	$^\circ C$	
T_{stg}	Storage Temperature	-65~200	$^\circ C$	



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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	BUX67	$I_C=200\text{mA}; I_B=0$	150			V
		BUX67A		250			
		BUX67B		300			
		BUX67C		350			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		$I_C=1\text{A}; I_B=0.15\text{A}$			2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		$I_C=1\text{A}; I_B=0.15\text{A}$			1.4	V
I_{CBO}	Collector Cutoff Current	BUX67	$V_{CB}=150\text{V}; I_E=0$			1.0	mA
		BUX67A	$V_{CB}=250\text{V}; I_E=0$			1.0	
		BUX67B	$V_{CB}=300\text{V}; I_E=0$			1.0	
		BUX67C	$V_{CB}=350\text{V}; I_E=0$			1.0	
I_{EBO}	Emitter Cutoff Current		$V_{EB}=6\text{V}; I_C=0$			0.5	mA
h_{FE}	DC Current Gain		$I_C=1\text{A}; V_{CE}=5\text{V}$	10		150	
f_T	Current Gain-Bandwidth Product		$I_C=0.5\text{A}; V_{CE}=10\text{V}$		25		MHz